

United States District Court,
D. New Jersey.

MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD,
Plaintiff.

v.

SAMSUNG ELECTRONICS CO., LTD., et al,
Defendants.

Samsung Electronics Co., Ltd., et al,
Counterclaimants.

v.

Matsushita Electric Industrial Co., Ltd,
Counterclaim Defendant.

Civ. No. 02-336 (GEB)

March 10, 2006.

Joseph A. Clark, Paul J. Halasz, Day Pitney, LLP, Morristown, NJ, for Plaintiff/Counterclaim Defendant.

Karen A. Confoy, Sterns & Weinroth, PC, Trenton, NJ, for Defendants.

MARKMAN ORDER

GARRETT E. BROWN, JR., District Judge.

This matter having come before the Court upon the parties' Motions for Claim Construction [Docket Entry 50-51] and Defendants' Motion to Seal Certain Confidential Documents [Docket Entry 87]; and the Court having considered the parties' written submissions; and the Court having conducted a *Markman* hearing in connection with the instant motions; and for the reasons set forth in the *Markman* Opinion accompanying this Order;

IT IS THIS 10th day of March, 2006 hereby

ORDERED that the disputed claim terms have the following meanings:

A. The '998 Patent

1. the corresponding structure for "means for reading" in Claims 1, 4 and 7 that performs the claimed function "to read data from a plurality of the memory cells connected to a specific word line into a plurality of data lines by activating the specific word line of the memory cell array" is the word line driver 3 and memory cells 13;
2. the sense amplifier consists of a plurality of differential amplifiers which may sense from more than one

memory cell array;

3. "sense amplifier driver" means "a circuit that is connected to a restore signal line and a drive signal line which provides voltages for operating the differential amplifiers";

4. "restore signal line" means "a line that is connected to both the sense amplifier driver and the differential amplifier through which an electric current, namely a restore signal, flows which causes the differential amplifiers to operate";

5. "drive signal line" means "a line that is connected to both the sense amplifier driver and the differential amplifier through which an electric current, namely a drive signal, flows which causes the differential amplifiers to operate";

6. "opposite ends" means "toward the termination point of the conductor lines";

B. The '095 Patent

7. "a plurality of unit memory cell blocks distributed through said memory array region at regular spacings" means "a regular distribution of a plurality of unit memory cell blocks in at least one direction";

8. "a plurality of unit sense amplifier blocks distributed among said unit memory cell blocks at regular spacings" means "a regular distribution of a plurality of unit sense amplifier blocks in at least one direction";

9. "a plurality of sense amplifier drive circuits, distributed among said unit sense amplifier blocks at regular spacings" means "a regular distribution of a plurality of sense amplifier circuits in at least one direction";

10. "an upper layer of a substrate" means "a layer, situated above a lower layer, which is part of the substrate";

11. "a lower layer of said substrate" means "a layer, situated below an upper layer, which is part of the substrate";

C. The '648 Patent

12. the corresponding structures for the "memory replacement means" in Claims 1 and 4 as disclosed in Embodiments I and III are the row predecoder 5, along with the redundancy-use decision circuit 20, the redundancy encoder 8, and the decode signal selection circuit 9 in Figures 1 and 7;

13. Embodiment II is not inoperative; the corresponding structures for the "memory replacement means" in Claims 1 and 4 as disclosed in Embodiment II is the redundancy-use decision circuit 20, the redundancy encoder 8, the circuit for generating the primary memory stop signal 18, and the memory cell block selection switching circuit 29 in Figure 6;

D. The '048 Patent

14. "edge portion" is "the two-dimensional border or boundary of the layer";

15. "recessed edge portion" requires the entire edge of the layer to be indented in its entirety;

16. "formed on" requires direct contact between the layer and the element following the term in the claim;

17. "layer" means "a thickness of material laid on, spread over, or otherwise covering a surface; a stratum";

18. "gate-insulating layer" is one particular layer that may consist of multiple layers;

19. the "gate structure having ..." term means that the gate structure consists of a first conductive layer of polycrystalline silicon and a second conductive layer of refractory metal silicide only, and may not include additional layers;

20. "refractory metal" means "a metal with a high melting point including titanium;" and it is further

ORDERED that Defendants' Motion to Seal [Docket Entry 87] is DENIED.

D.N.J.,2006.

Matsushita Electric Indus. Co., Ltd. v. Samsung Electronics Co., Ltd.

Produced by Sans Paper, LLC.